Abstracts

Monolithic GaAs p-i-n Diode Switch Circuits for High-Power Millimeter-Wave Applications (Short Papers)

J.V. Bellantoni, D.C. Bartle, D. Payne, G. McDermott, S. Bandla, R. Tayrani and L. Raffaelli. "Monolithic GaAs p-i-n Diode Switch Circuits for High-Power Millimeter-Wave Applications (Short Papers)." 1989 Transactions on Microwave Theory and Techniques 37.12 (Dec. 1989 [T-MTT] (1989 Symposium Issue)): 2162-2165.

Two different Ku-band SPDT switch circuits using monolithic GaAs epitaxial p-i-n diode technology are presented. The lowest insertion loss is 0.7 dB at 35 GHz, and isolation is better than 32 dB from 30 to 40 GHz. The power handling capability is at least +38 dBm pulsed and +35 dBm CW. Switching speed rise and fall times are 2 ns.

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